

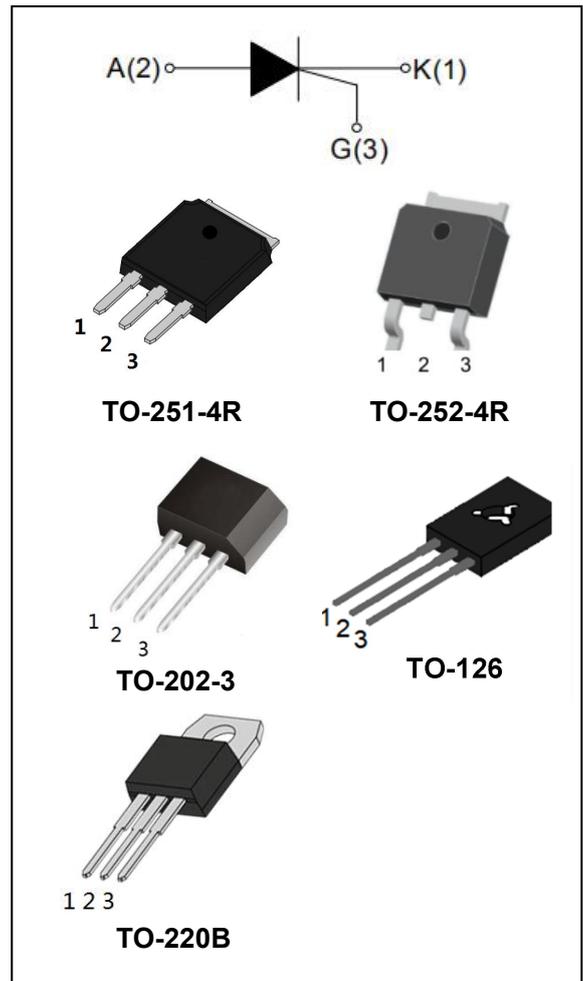


# Jiangsu Weida Semiconductor Co., Ltd.

## X0405 4A Sensitive SCRs

### DESCRIPTION:

The X0405 SCR series provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on straight hair, igniter etc.



### MAIN FEATURES:

symbol	value	unit
$I_{T(RMS)}$	4	A
$I_{GT}$	$\leq 200$	$\mu A$
$V_{DRM}/V_{RRM}$	600/800	V

### ABSOLUTE MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40~150	$^{\circ}C$
Operating junction temperature range	$T_j$	-40~110	$^{\circ}C$
Repetitive peak off-state voltage ( $T_j=25^{\circ}C$ )	$V_{DRM}$	600/800	V
Repetitive peak reverse voltage ( $T_j=25^{\circ}C$ )	$V_{RRM}$	600/800	V
RMS on-state current	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, $F=50Hz$ )	$I_{TSM}$	30	A
$I^2t$ value for fusing ( $t_p=10ms$ )	$I^2t$	4.5	$A^2s$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )	$di/dt$	50	$A/\mu s$
Peak gate current	$I_{GM}$	1.2	A



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Average gate power dissipation	$P_{G(AV)}$	0.2	W
Peak gate power	$P_{GM}$	2	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN	TYPE	MAX	
$I_{GT}$	$V_D=12\text{V}, R_L=33\Omega$	-	50	200	$\mu\text{A}$
$V_{GT}$		-	0.6	0.8	V
$V_{GD}$	$V_D=V_{DRM} T_j=110^\circ\text{C}$ $R_L=3.3\text{k}\Omega$	0.2	-	-	V
$I_H$	$I_T=50\text{mA}$	-	-	5	mA
$I_L$	$I_G=1.2I_{GT}$	-	-	6	mA
dV/dt	$V_D=0.66 \times V_{DRM} T_j=110^\circ\text{C}$ Gate open $R_{GK}=1\text{k}\Omega$	10	-	-	V/ $\mu\text{s}$

**STATIC CHARACTERISTICS**

Symbol	Test Condition		Value	Unit
$V_{TM}$	$I_{TM}=8\text{A} t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	MAX	1.5 V
$I_{DRM}$ $I_{RRM}$	$V_{DRM}=V_{RRM}$ $R_{GK}=1\text{k}\Omega$	$T_j=25^\circ\text{C}$	MAX	5 $\mu\text{A}$
		$T_j=110^\circ\text{C}$		100 $\mu\text{A}$

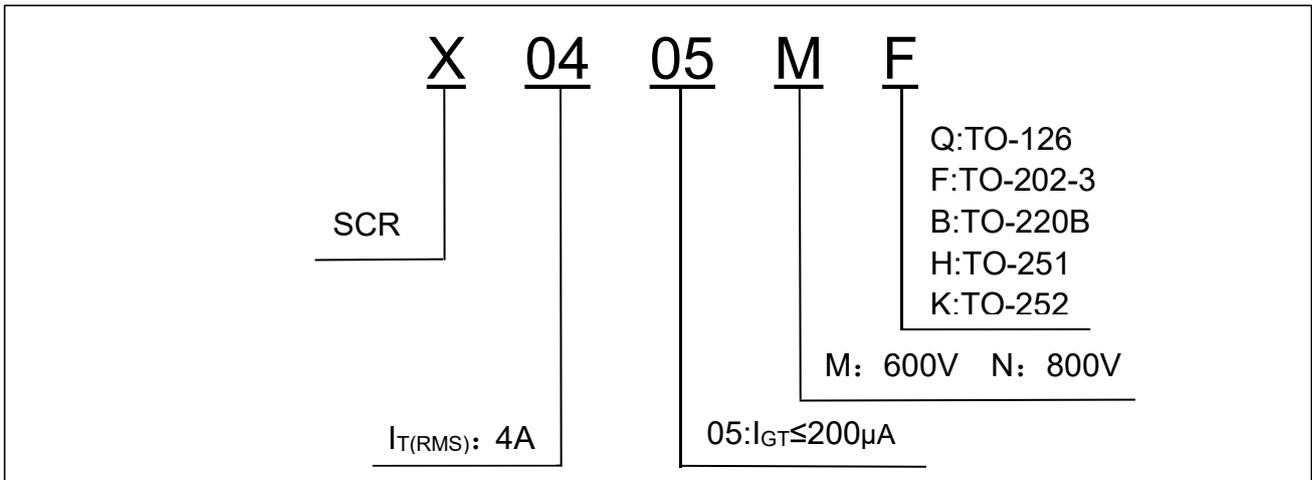
**THERMAL RESISTANCES**

Symbol	Test Condition		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-202-3	7.8	$^\circ\text{C/W}$
		TO-252-4R	6.5	
		TO-126	7.3	
		TO-220B	3.0	

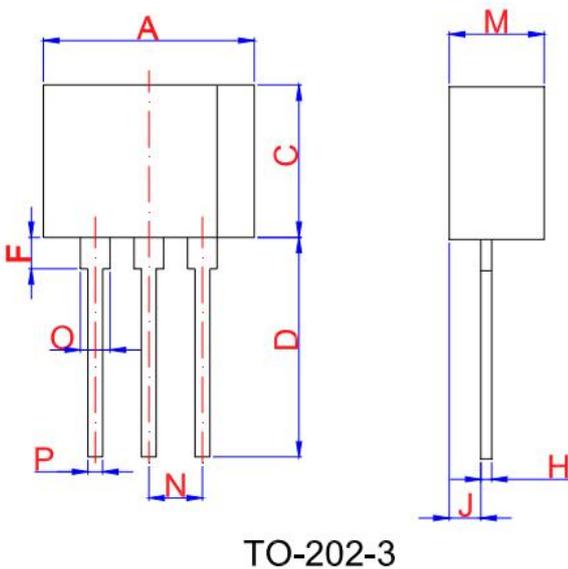


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**ORDERING INFORMATION**



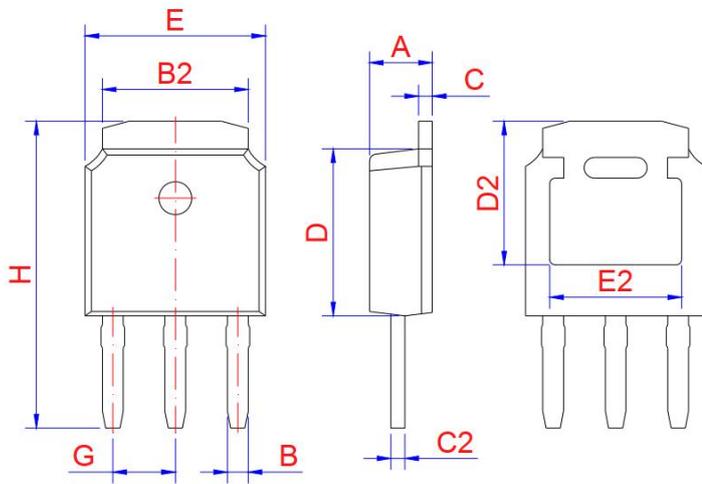
**PACKAGE MECHANICAL DATA**



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.30		9.90	0.366		0.39
C	7.00		7.60	0.276		0.299
D	10.5		11.50	0.413		0.453
F	1.50		2.50	0.059		0.098
H	0.45		0.55	0.018		0.022
J	1.50		1.90	0.059		0.075
M	4.40		4.70	0.173		0.185
N	2	2.54			0.100	
O	1.20		1.50	0.047		0.059
P	0.60		0.80	0.024		0.031

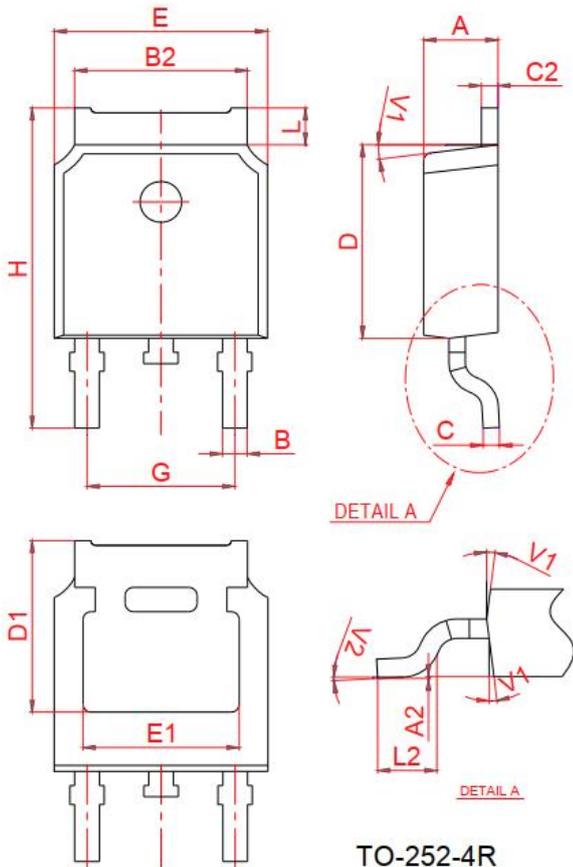


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TO-251-4R

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10	2.30	2.50	0.083	0.091	0.098
B	0.66	0.76	0.86	0.026	0.030	0.034
B2	5.15	5.33	5.48	0.203	0.210	0.216
C	0.44	0.51	0.58	0.017	0.020	0.023
C2	0.44	0.51	0.58	0.017	0.020	0.023
D	5.90	6.10	6.30	0.232	0.240	0.248
D2	5.30REF			0.209REF		
E	6.40	6.60	6.80	0.252	0.260	0.268
E2	4.83REF			0.190REF		
G	2.19	2.29	2.39	0.086	0.090	0.094
H	10.60	11.20	11.80	0.417	0.441	0.465

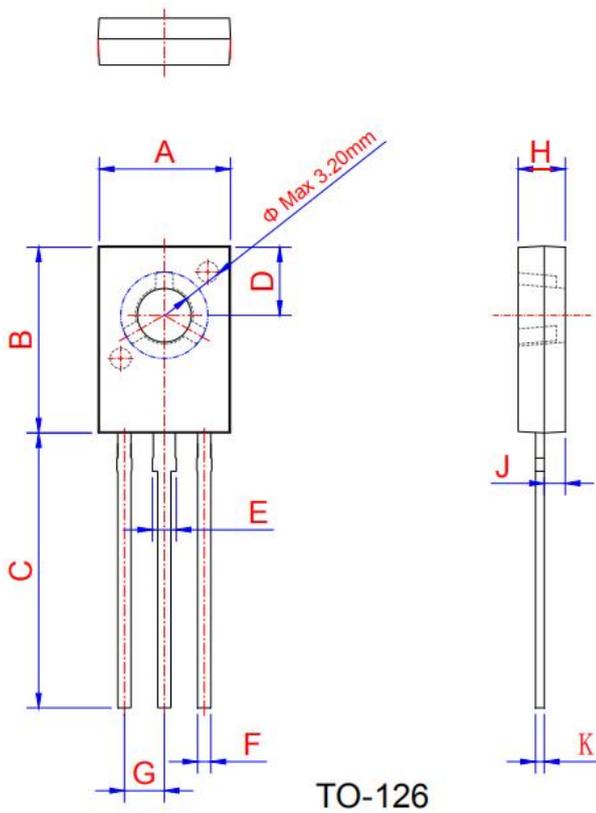


TO-252-4R

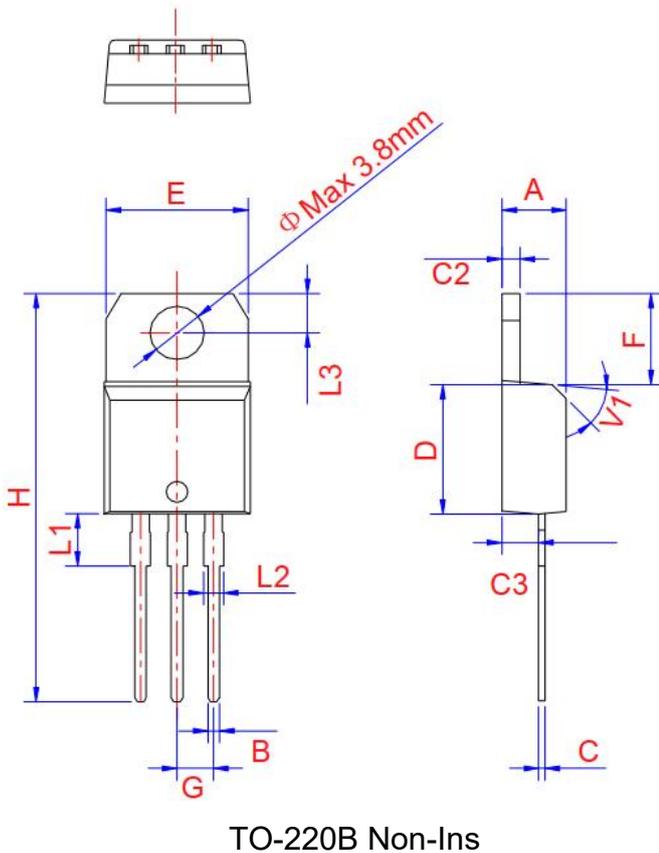
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.2		2.4	0.087		0.094
A2	0		0.1	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.1		5.46	0.201		0.215
C	0.46		0.58	0.018		0.023
C2	0.44		0.58	0.017		0.023
D	5.9		6.3	0.232		0.248
D1	5.30REF			0.211REF		
E	6.4		6.8	0.252		0.268
E1	4.63			0.182		
G	4.372		4.772	0.172		0.188
H	9.8		10.4	0.386		0.409
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°	0°		6°



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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.4		7.8	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.9		4.1	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G		2.29			0.09	
H	2.5		2.9	0.098		0.114
K	0.45		0.6	0.018		0.024



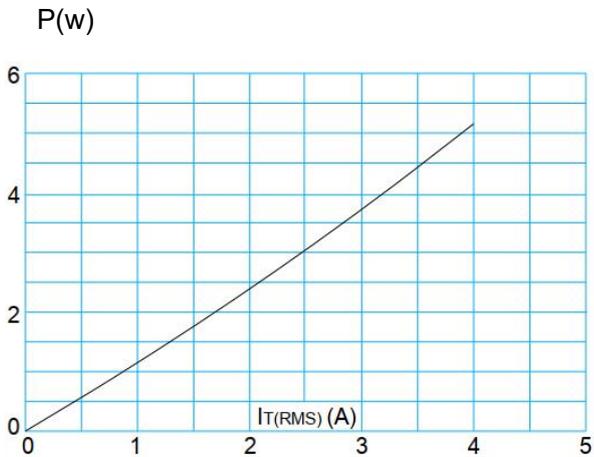
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4	4.47	4.6	0.173	0.176	0.181
B	0.61		0.88	0.024		0.035
C	0.46	0.50	0.7	0.018	0.02	0.028
C2	1.21	1.27	1.32	0.048	0.050	0.052
C3	2.4		2.72	0.094		0.107
D	8.6		9.7	0.339		0.382
E	9.8		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.7	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



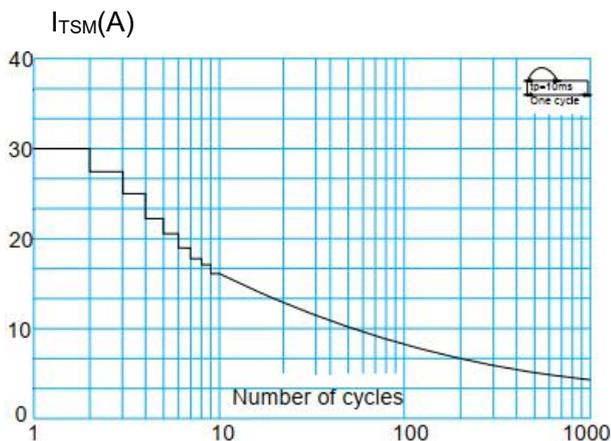
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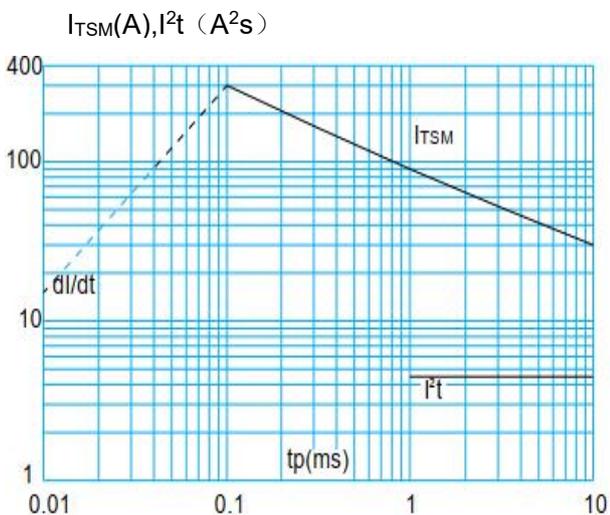
**FIG.1:** Maximum power dissipation versus RMS on-state current



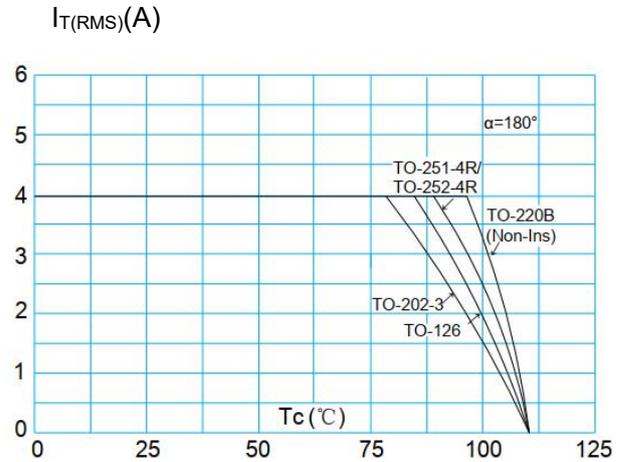
**FIG.3:** Surge peak on-state current versus number of cycles



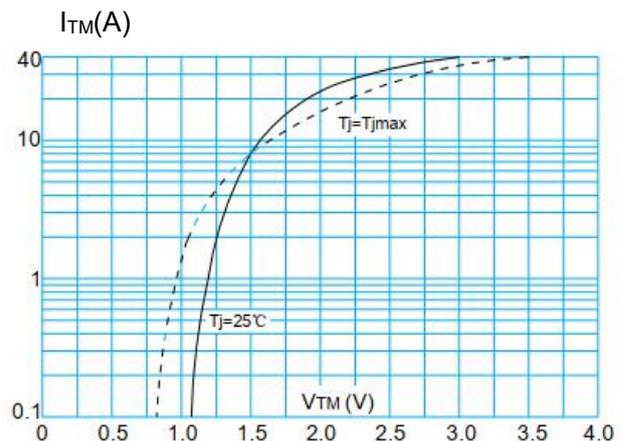
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2 t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )



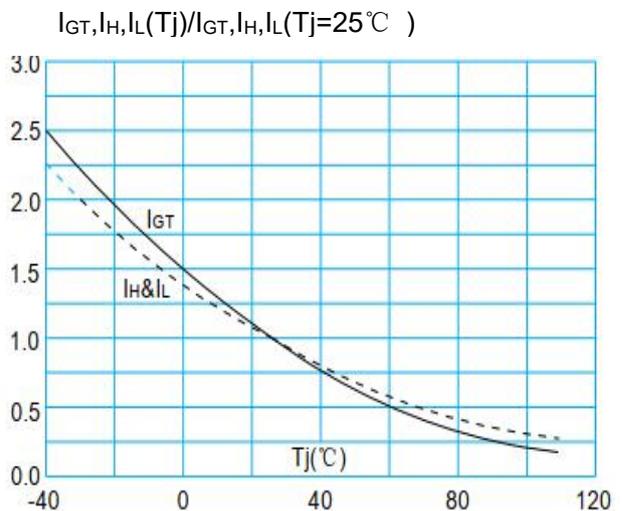
**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature





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